

isc Silicon NPN Power Transistor

2SC4368

DESCRIPTION

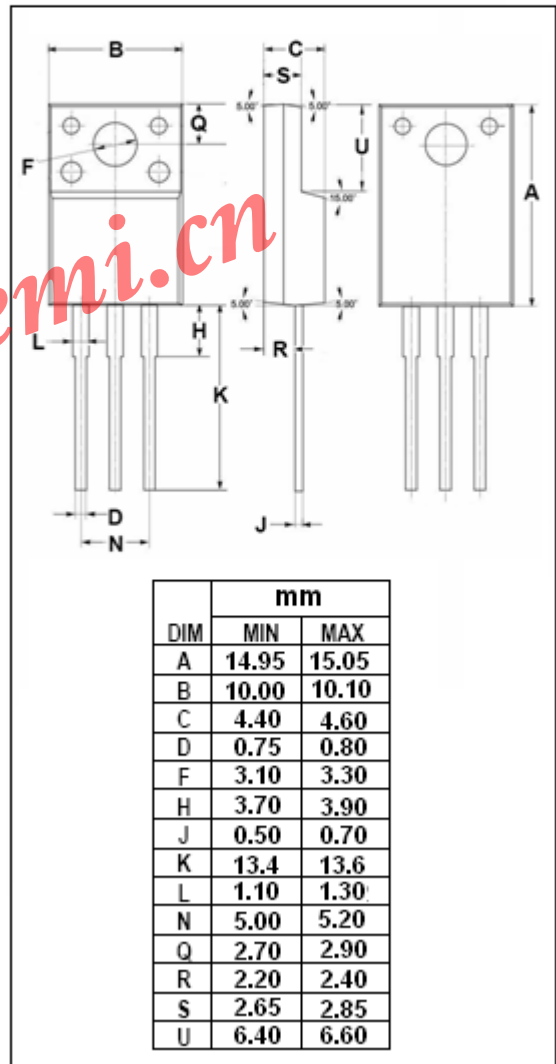
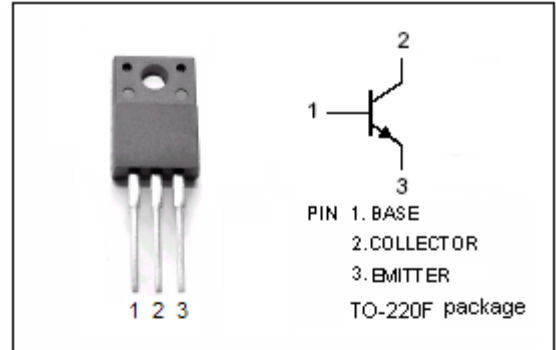
- Collector-Emitter Breakdown Voltage
: $V_{CEO} = 150V(\text{Min})$
- Complement to Type 2SA1657

APPLICATIONS

- Designed for TV, monitor vertical output applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current-Continuous	1.5	A
I_B	Base Current-Continuous	0.5	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	20	W
	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	2	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SC4368****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; I _B = 0	150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 500mA; I _B = 50mA			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 120V; I _E = 0			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μ A
h _{FE}	DC Current Gain	I _C = 500mA; V _{CE} = 10V	40		140	
C _{OB}	Collector Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1.0MHz		35		pF
f _T	Current-Gain—Bandwidth Product	I _C = 500mA; V _{CE} = 10V		4		MHz

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